

Title (en)

PRODUCTION PROCESS OF A NON-LINEAR VOLTAGE-DEPENDENT RESISTOR

Publication

EP 0357113 A3 19900321 (DE)

Application

EP 89201988 A 19890728

Priority

DE 3826356 A 19880803

Abstract (en)

[origin: EP0357113A2] A method for manufacturing a voltage-dependent, non-linear resistor having a ceramic sinter body on the basis of the oxides of titanium, bismuth and zinc oxide containing at least one transition metal as resistor material, the sinter body being manufactured by shaping the powdery resistor material and subsequently sintering in air at a temperature in the range of 1,200 to 1,350 DEG C and subsequently being fitted with electrodes, grains being added to the powdery resistor material from resistor material of a medium grain size in the range of 4 to 12 mu m m prefired at a temperature in the range of 1,200 to 1,400 DEG C and in a quantity of 1 to 50% by weight. <IMAGE>

IPC 1-7

H01C 7/10; **H01C 17/30**

IPC 8 full level

H01C 7/10 (2006.01); **H01C 7/112** (2006.01); **H01C 17/30** (2006.01)

CPC (source: EP KR)

H01C 7/10 (2013.01 - KR); **H01C 7/112** (2013.01 - EP); **H01C 17/30** (2013.01 - EP)

Citation (search report)

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- [A] PATENT ABSTRACTS OF JAPAN, Band 3, Nr. 78 (E-121), 5. Juli 1979, Seite 148 E 121; & JP-A-54 57 699 (MATSUSHITA DENKI SANGYO K.K.) 09-05-1979
- [A] CHEMICAL ABSTRACTS, Band 104, Nr. 20, Mai 1986, Seite 672, Zusammenfassung Nr. 178543h, Columbus, Ohio, US; & JP-A-60 169 103 (MEIDENSHA ELECTRIC Mfg. CO., LTD) 02-09-1985

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DOCDB simple family (application)

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